

**/ Descriptions**

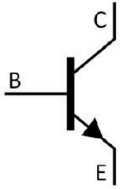
JF K\$\*) \* E GE Silicon NPN transistor in a SOT-323 Plastic Package.

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Complementary pair with 8550W.

Power amplifier applications.

**/ Equivalent Circuit**



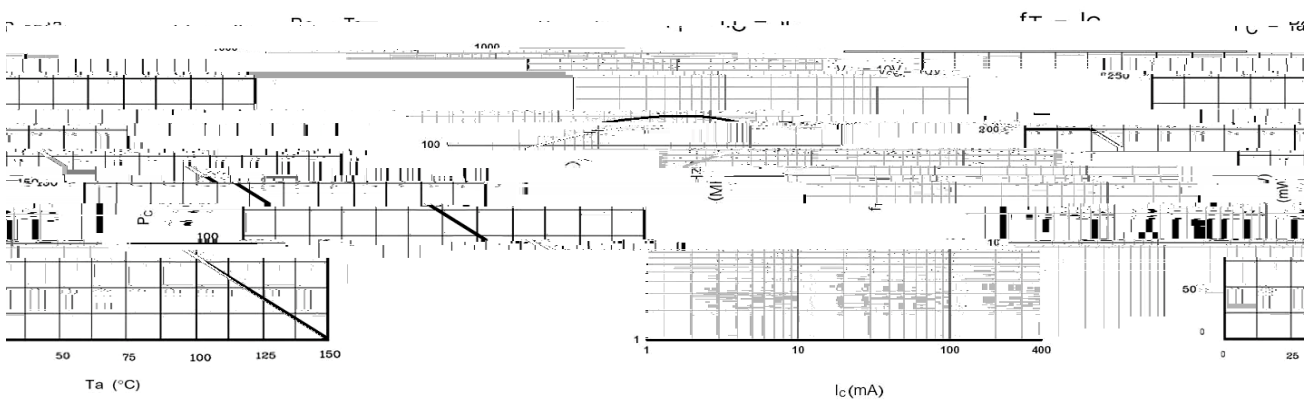
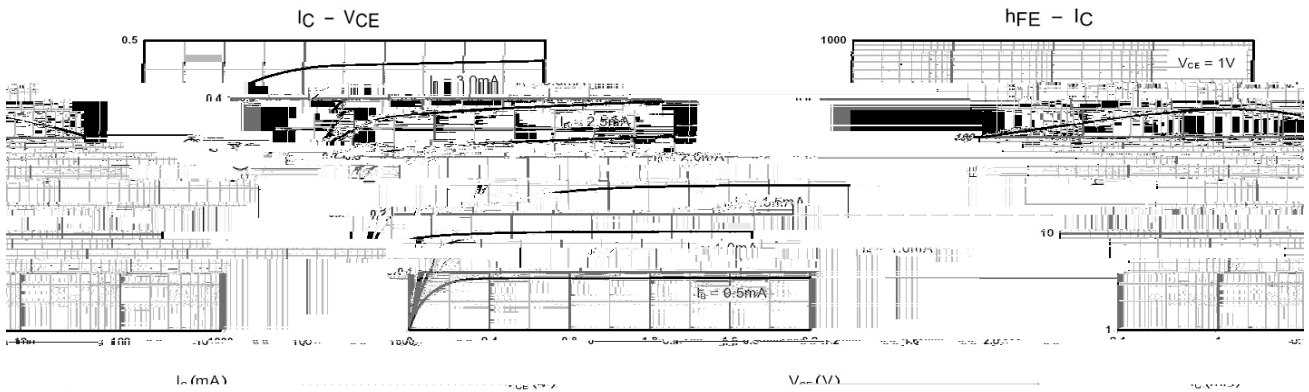
PIN1 Emitter      PIN 2 Base      PIN 3 Collector

**/ Marking**

$h_{FE}$ Classifications Symbol	B	C	D
$h_{FE}$ Range	85 160	120 200	160 300
Marking	HY1B	HY1C	HY1D

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	40	V
Collector to Emitter Voltage	$V_{CEO}$	25	V
Emitter to Base Voltage	$V_{EBO}$	5.0	V
Collector Current - Continuous	$I_C$	1.5	A
Base Current	$I_B$		

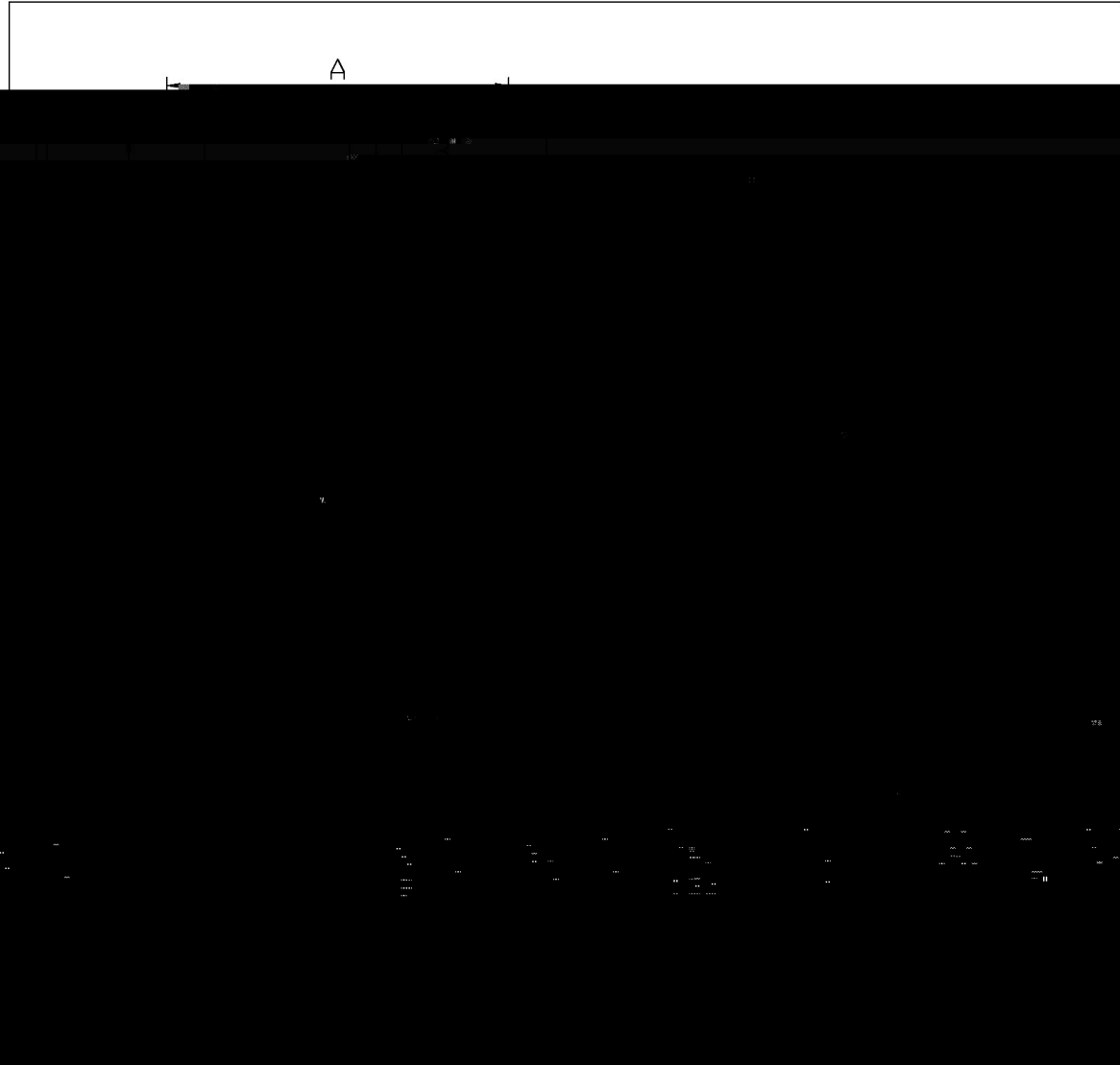
/ Electrical Characteristic Curve



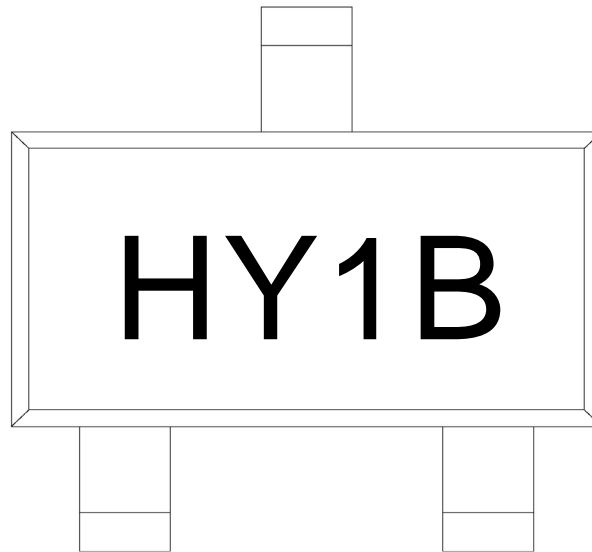
/ Package Dimensions

SOT-323

单位; mm



/ Marking Instructions

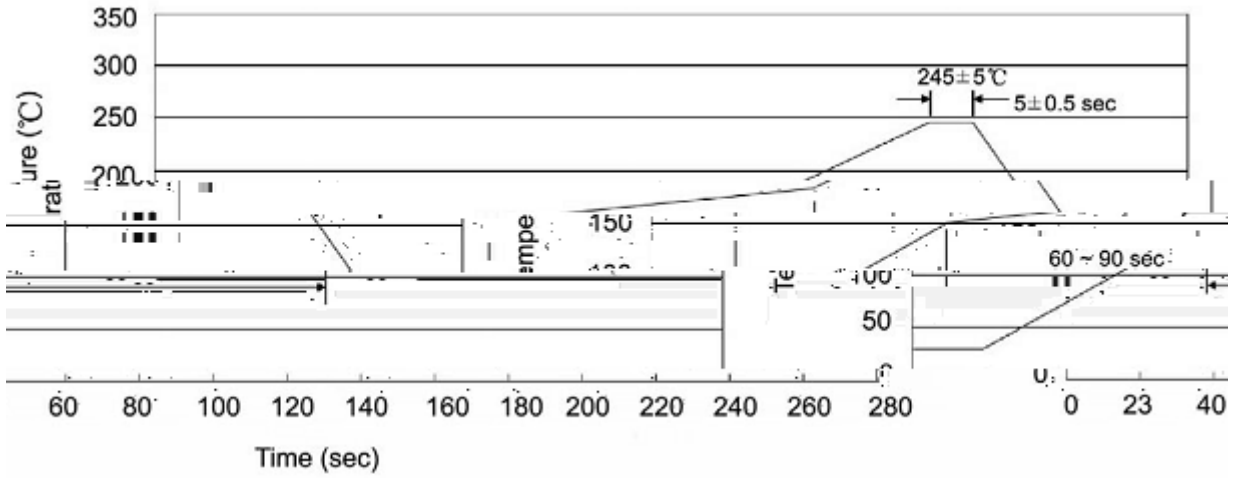


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Note:

- H: Company Code.
- Y1: Product Type.
- B  $h_{FE}$  Classifications Symbol

( ) / Resistance to Soldering Heat Test Conditions



Note:

- |   |        |     |            |        |   |
|---|--------|-----|------------|--------|---|
| 1 | 25     | 150 | 60         | 90sec; | 1.Preheating:25~150 , Time:60~90sec.      |
| 2 | 245..5 |     | 5..0.5sec; |        | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 |        | 2   | 10         | /sec.  | 3. Cooling Speed: 2~10 /sec.              |

/ Resistance to Soldering Heat Test Conditions

260..5      10..1 sec.      Temp.:260±5      Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm <sup>3</sup> )
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